

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	lim near victo.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:44
L2	22	lim near victor.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:44
L3	237	chen near feng.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:44
L4	186	chan near lap.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:45
L5	803	438/296.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:45
L6	177440	"438"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:46
L7	71	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidation near mask) and (oxidiz\$3) nnear3 (substrate or wafer) and (polish\$3) near5 (oxide near3 liner).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:59
L8	105	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidation near mask) and (oxidiz\$3) nnear3 (substrate or wafer) and (polish\$3) near5 (oxide near3 liner)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:59

L9	1	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidiz\$3) near3 (substrate or wafer) and (polish\$3) near5 (oxide near3 liner)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:00
L10	0	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidation near mask) and (oxidiz\$3) near3 (substrate or wafer) and (polish\$3) near5 (oxide near3 liner).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 10:59
L11	13	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidation near mask) and (oxidiz\$3) near3 (substrate or wafer) and (polish\$3) near5 (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:09
L12	280	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon) and (oxidiz\$3) near3 (substrate or wafer) and (polish\$3) near5 (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:36
L13	1037	((shallow near trench near isolation) or (sti)) and (silicon near nitride or sin) and (polysilicon or poly-silicon) and (oxidiz\$3) near3 (substrate or wafer) and (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:36
L14	243369	13 and (polysilicon or poly-silicon)ith (silicon near nitride or sin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:37
L15	402	13 and (polysilicon or poly-silicon) with (silicon near nitride or sin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:37
L16	40676	14 and ((polish\$3) or (cmp))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:38
L17	316	15 and ((polish\$3) or (cmp))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:54

L18	25543	((polish\$3) or (cmp)) with (oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:55
L19	1883	((polish\$3) or (cmp)) with (oxide) with ((polysilicon) or (poly near silicon) or (poly-silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:57
L20	300	19 and (oxidiz\$3) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:58
L21	102	20 and ((sti) or (shallow near trench near isolation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/09 11:58